

HXMC65N300H3

N-Channel SiC Power MOSFET MOSFET

Features

- High Blocking Voltage with Low On-Resistance
- High Speed Switching with Low Capacitance
- Easy to Parallel and Simple to Drive
- 15V / 0V V_{GS} compatible with most flyback controllers

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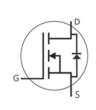
- Higher System Efficiency
- Reduced Cooling Requirements
- **Increased Power Density**
- Increased System Switching Frequency

Applications

- Solar and UPS inverters
- On Board Charger
- High voltage DC/DC converters
- Switched mode power supplies
- Load switch
- LED/LCD/PDP TV and monitor Lighting

Parar	neter	Value	Unit	
V _{DS}		650	V	
R _{DS(on)_typ.}	V _{GS} =18V	300	mΩ	
<i>I</i> _D		10	Α	







Maximum Ratings (T_C=25°C unless otherwise specified)

Symbol	Parameter	Value	Unit	Test Conditions	Note
V _{DSmax}	Drain-Source Voltage	650	V	V _{GS} =0V, I _D =500μA	
V _{GSmax}	Gate-Source Voltage	-8/+20	V	Absolute maximum values	
V_{GSop}	Gate-Source Voltage	-50/+15	V	Recommended operational values	
	David Comment	10	_	V _{GS} =15V, T _c =25°C	Fig. 19
I _D	Continuous Drain Current	7	Α	V _{GS} =15V, T _c =100°C	
I _{D(pulse)}	Pulsed Drain Current	25	Α	Pulse width t _p limited by T _{Jmax}	
P _D	Power Dissipation	75	w	T _c =25°C, T _J =175°C	Fig. 20
T _J , T _{STG}	Operating Junction and Storage Temperature	-55 to +175	°C		
T∟	Solder Temperature, 1.6mm from case for 10s	260	°C		





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Electrical Characteristics (T_C=25°C unless otherwise specified)

Symbol	Parameter	Min.	Тур.	Max.	Unit	Test Conditions	Note	
V _{(BR)DSS}	Drain-Source Breakdown Voltage	650	/	/	V	V _{GS} =0V, I _D =500μA		
V	V _{GS(th)} Gate Threshold Voltage		3.2	4.0	v	V _{DS} =V _{GS} , I _D =1.4mA	Fig. 11	
$V_{GS(th)}$	Gate inreshold voltage	/	2.4	/]	V _{DS} =V _{GS} , I _D =1.4mA, T _J =175°C	Fig. 11	
I _{DSS}	Zero Gate Voltage Drain Current	/	/	10	μΑ	V _{DS} =650V, V _{GS} =0V		
I _{GSS+}	Gate-Source Leakage Current	/	/	50	nA	V _{DS} =0V, V _{GS} =20V		
I _{GSS-}	Gate-Source Leakage Current	/	/	50	nA	V _{DS} =0V, V _{GS} =-8V		
		/	380	530	mΩ	V _{GS} =15V, I _D =5A		
	Busin Sauras On State Basistan	/	468	/	mΩ	V _{GS} =15V, I _D =5A, T _J =175℃	Fig.	
$R_{DS(on)}$	Drain-Source On-State Resistance	/	300	420	mΩ	V _{GS} =18V, I _D =5A	4,5,6	
		/	370	/	mΩ	V _{GS} =18V, I _D =5A, T _J =175℃	7	
		/	3.1	/		V _{DS} =20V, I _{DS} =5A	Fig. 7	
g fs	Transconductance	/	2.8	/	S	V _{DS} =20V, I _{DS} =5A, T _J =175℃		
C _{iss}	Input Capacitance	/	224	/		V _{GS} =0V		
C _{oss}	Output Capacitance	/	10.5	/	рF	V _{DS} =400V	Fig.	
C _{rss}	Reverse Transfer Capacitance	/	1.1	/		f=1MHz	17,18	
E _{oss}	C _{oss} Stored Energy	/	1.3	/	μ	V _{AC} =25mV	Fig. 16	
E _{ON}	Turn-On Switching Energy	/	12	/		V _{DS} =400V, V _{GS} =0V/15V		
E _{OFF}	Turn-Off Switching Energy	/	8	/	μ	I _D =5A, R _{G(ext)} =2.5Ω, L=100μH		
t _{d(on)}	Turn-On Delay Time	/	5.5	/				
t _r	Rise Time	/	4.3	/	1	V _{DS} =400V, V _{GS} =0V/15V, I _D =5A		
t _{d(off)}	Turn-Off Delay Time	/	9.1	/	ns $R_{G(ext)}=2.5\Omega$, $R_L=160\Omega$			
t _f	Fall Time	/	7.3	/	1			
R _{G(int)}	Internal Gate Resistance	/	12	/	Ω	f=1MHz, V _{AC} =25mV		
Q _{GS}	Gate to Source Charge	/	2.3	/		V _{DS} =400V		
\mathbf{Q}_{GD}	Gate to Drain Charge	/	1.9	/	nC V _{GS} =0V/15V		Fig. 12	
Q _G	Total Gate Charge	/	6.3	/	1	I _D =5A		

Reverse Diode Characteristics

Symbol	Parameter	Тур.	Max.	Unit	Test Conditions	Note
V	V Binds Famound Valtage		/	V	V_{GS} =-5V, I_{SD} =2.5A, T_{J} =25 $^{\circ}$ C	Fig.
V _{SD}	Diode Forward Voltage	3.6	/	v	V _{GS} =-5V, I _{SD} =2.5A, T _J =175 ℃	8,9,10
Is	Continuous Diode Forward Current	/	8	Α	T _C =25°C	
t _{rr}	Reverse Recover Time	8.2	/	ns		
Q _{rr}	Reverse Recovery Charge	14.1	/	nC	V _R =400V, I _{SD} =2.5A	
I _{rrm}	Peak Reverse Recovery Current	0.9	/	Α		





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Thermal Characteristics

Symbol	Parameter	Тур.	Max.	Unit	Test Conditions	Note
$R_{\theta JC}$	Thermal Resistance from Junction to Case	2	/	°C/W		
$R_{\theta JA}$	Thermal Resistance from Junction to Ambient	/	40	C/W		



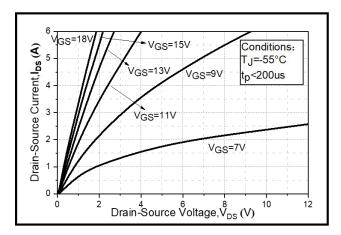


Figure 1. Output Characteristics T_J = -55°C

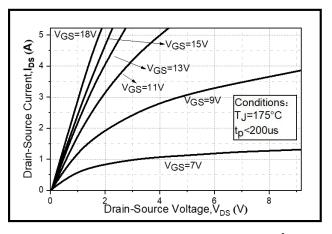


Figure 3. Output Characteristics T_J = 175°C

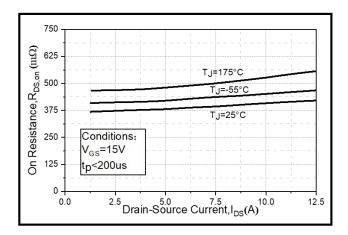


Figure 5. On-Resistance vs. Drain Current For Various **Temperatures**

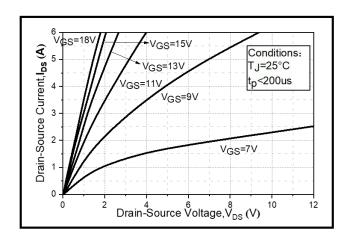


Figure 2. Output Characteristics T_J = 25°C

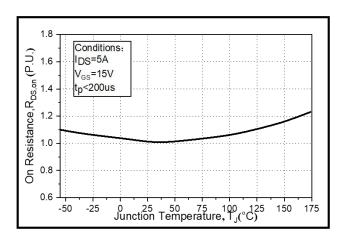


Figure 4. Normalized On-Resistance vs. Temperature

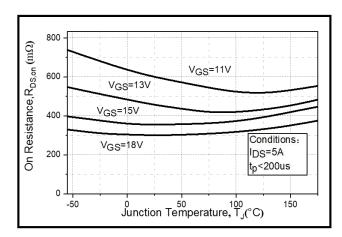


Figure 6. On Resistance vs. Temperature For Various Gate Voltage



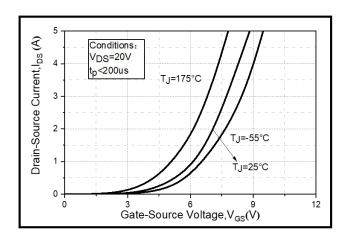


Figure 7. Transfer Characteristic for Various Junction Temperatures

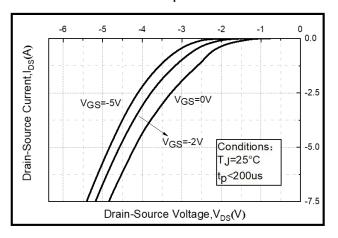


Figure 9. Body Diode Characteristic at 25°C

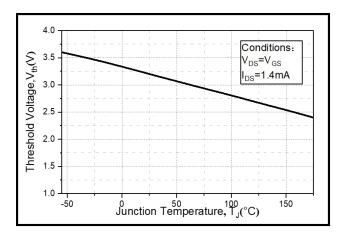


Figure 11. Threshold Voltage vs. Temperature

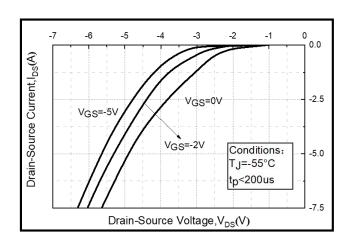


Figure 8. Body Diode Characteristic at -55°C

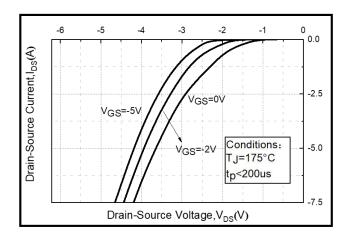


Figure 10. Body Diode Characteristic at 175°C

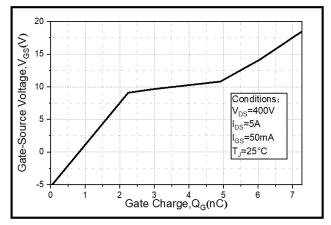


Figure 12. Gate Charge Characteristics



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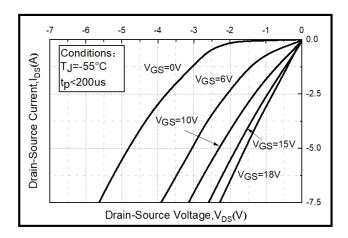


Figure 13. 3rd Quadrant Characteristic at -55°C

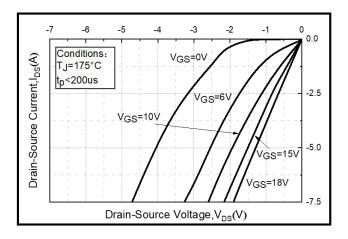


Figure 15. 3rd Quadrant Characteristic at 175°C

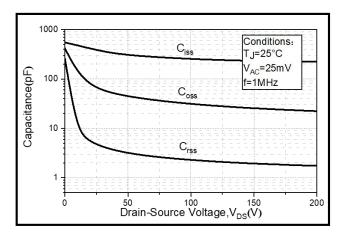


Figure 17. Capacitances vs. Drain-Source Voltage (0 - 200V)

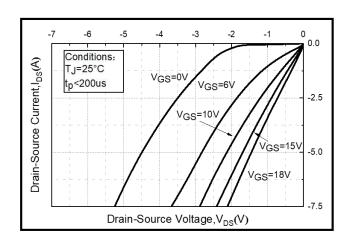


Figure 14. 3rd Quadrant Characteristic at 25°C

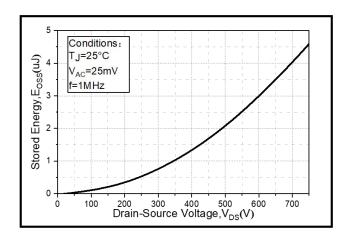


Figure 16. Output Capacitor Stored Energy

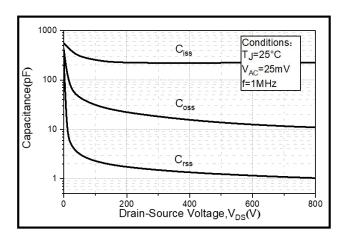


Figure 18. Capacitances vs. Drain-Source Voltage (0 - 800V)



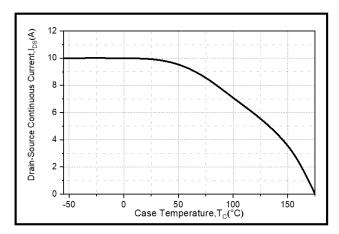


Figure 19. Continuous Drain Current vs. **Case Temperature**

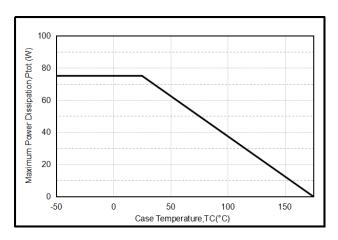


Figure 20. Maximum Power Dissipation vs. **Case Temperature**



Test Circuit Schematic

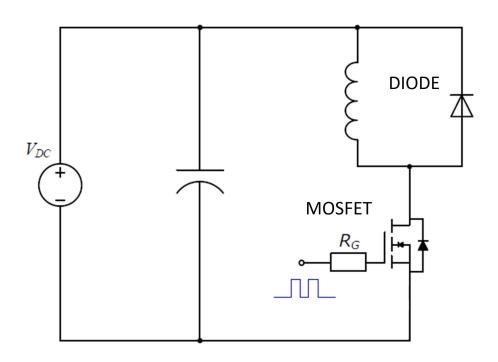
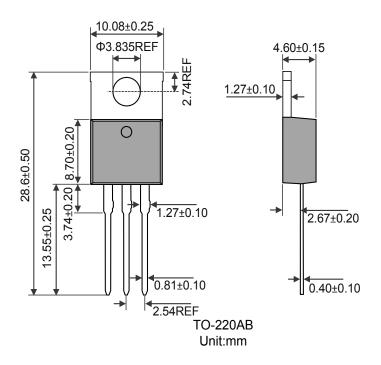


Figure 21. Clamped Inductive Switching **Waveform Test Circuit**





Package Outline Dimensions



Marking Information



"MHCHXM"= Product Logo
"Marking Code"= The Following
"XXXX"= Date Code Marking

Marking Code	Part Number
C65N300H3	HXMC65N300H3

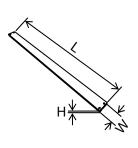




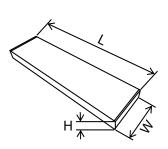
Packing Information

Packaging	Part Number	Quantity(pcs)	Size(mm)
	Tube	50	L534×W33×H7
Tube	Inner Box	1000	L560×W150×H40
	Outer Box	5000	L580×W235×H175

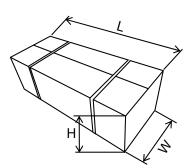
Packaging:Tube







Tube Inner Box



Tube Outer Box





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